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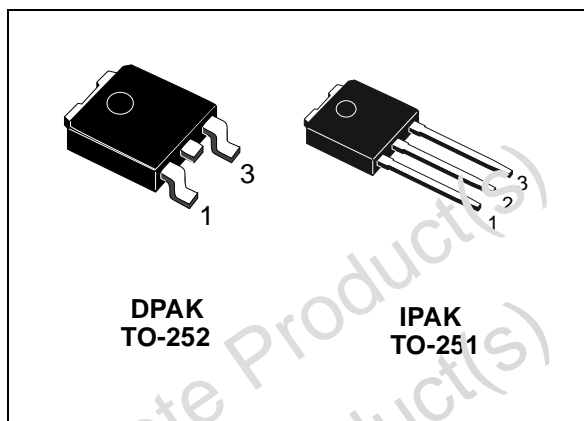


STD3NM50 STD3NM50-1

N-CHANNEL 550V @ Tjmax- 2.5Ω - 3A DPAK/IPAK
 Zener-Protected MDmesh™ MOSFET

| TYPE | V _{DSS} (@Tjmax) | R _{DS(on)} | I _D |
|------------|------------------------------|---------------------|----------------|
| STD3NM50 | 550V | < 3 Ω | 3 A |
| STD3NM50-1 | 550V | < 3 Ω | 3 A |

- TYPICAL R_{DS(on)} = 2.5 Ω
- HIGH dv/dt AND AVALANCHE CAPABILITIES
- IMPROVED ESD CAPABILITY
- LOW INPUT CAPACITANCE AND GATE CHARGE
- LOW GATE INPUT RESISTANCE
- TIGHT PROCESS CONTROL AND HIGH MANUFACTURING YIELDS

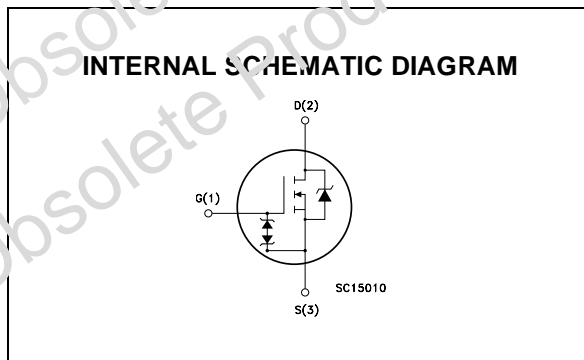


DESCRIPTION

The MDmesh™ is a new revolutionary MOSFET technology that associates the Multiple Drain process with the Company's PowerMESH™ horizontal layout. The resulting product has an outstanding low on-resistance, impressively high dv/dt and excellent avalanche characteristics. The adoption of the Company's proprietary strip technique yields overall dynamic performance that is significantly better than that of similar competition's products.

APPLICATIONS

The MDmesh™ family is very suitable for increase the power density of high voltage converters allowing system miniaturization and higher efficiencies.



ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|-----------------------|------------------------------------------------------|------------|------|
| V _{GS} | Gate- source Voltage | ±30 | V |
| I _D | Drain Current (continuous) at T _C = 25°C | 3 | A |
| I _D | Drain Current (continuous) at T _C = 100°C | 1.89 | A |
| I _{DM} (●) | Drain Current (pulsed) | 12 | A |
| P _{TOT} | Total Dissipation at T _C = 25°C | 46 | W |
| V _{ESD(G-S)} | Gate source ESD (HBM-C=100pF, R=15KΩ) | 4 | KV |
| | Derating Factor | 0.37 | W/°C |
| dv/dt(1) | Peak Diode Recovery voltage slope | 15 | V/ns |
| T _{stg} | Storage Temperature | -65 to 150 | °C |
| T _j | Max. Operating Junction Temperature | 150 | °C |

(*)Pulse width limited by safe operating area

(1) I_{SD} < 3A, di/dt < 400A/μs, V_{DD} < V_{(BR)DSS}, T_J < T_{JMAX}

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THERMAL DATA

| | | | |
|----------------|------------------------------------------------|------|------|
| Rthj-case | Thermal Resistance Junction-case Max | 2.73 | °C/W |
| Rthj-amb | Thermal Resistance Junction-ambient Max | 62.5 | °C/W |
| T _I | Maximum Lead Temperature For Soldering Purpose | 300 | °C |

AVALANCHE CHARACTERISTICS

| Symbol | Parameter | Max Value | Unit |
|-----------------|----------------------------------------------------------------------------------------------------------------------------|-----------|------|
| I _{AR} | Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max) | 1 | A |
| E _{AS} | Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V) | 130 | mJ |

ELECTRICAL CHARACTERISTICS (T_{CASE} = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|----------------------|-------------------------------------------------------|---------------------------------------------------------------------------------------|------|------|---------|----------|
| V _{(BR)DSS} | Drain-source Breakdown Voltage | I _D = 1 mA, V _{GS} = 0 | 500 | | | V |
| I _{DSS} | Zero Gate Voltage Drain Current (V _{GS} = 0) | V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C | | | 1 10 | μA μA |
| I _{GSS} | Gate-body Leakage Current (V _{DS} = 0) | V _{GS} = ± 20V | | | ± 5 | μA |

ON (1)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------------|-----------------------------------|------------------------------------------------------------|------|------|------|------|
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} = V _{GS} , I _D = 250μA | 3 | 4 | 5 | V |
| R _{DS(on)} | Static Drain-source On Resistance | V _{GS} = 10V, I _D = 1.5A | | 2.5 | 3 | Ω |

DYNAMIC

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------------|------------------------------|-----------------------------------------------------------------------------------------|------|------|------|------|
| g _{fs} (1) | Forward Transconductance | V _{DS} > I _{D(on)} × R _{DS(on)} max, I _D = 3 A | | 0.7 | | S |
| C _{iss} | Input Capacitance | V _{DS} = 25V, f = 1 MHz, V _{GS} = 0 | | 140 | | pF |
| C _{oss} | Output Capacitance | | | 40 | | pF |
| C _{rss} | Reverse Transfer Capacitance | | | 4 | | pF |
| R _G | Gate Input Resistance | f=1 MHz Gate DC Bias = 0 Test Signal Level = 20mV Open Drain | | 4 | | Ω |

Note: 1. Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %.

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ELECTRICAL CHARACTERISTICS (CONTINUED) SWITCHING ON

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|-------------|--------------------|------------------------------------------------------------------------------------------------|------|------|------|------|
| $t_{d(on)}$ | Turn-on Delay Time | $V_{DD} = 250V, I_D = 1.5A$ $R_G = 4.7\Omega, V_{GS} = 10V$ (see test circuit, Figure 3) | | 7 | | ns |
| t_r | Rise Time | | | 10 | | ns |
| Q_g | Total Gate Charge | $V_{DD} = 400V, I_D = 3A,$ $V_{GS} = 10V$ | | 5.5 | | nC |
| Q_{gs} | Gate-Source Charge | | | 2.5 | | nC |
| Q_{gd} | Gate-Drain Charge | | | 2.4 | | nC |

SWITCHING OFF

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------|-----------------------|-----------------------------------------------------------------------------------------------|------|------|------|------|
| $t_{r(Voff)}$ | Off-voltage Rise Time | $V_{DD} = 480V, I_D = 3A,$ $R_G = 4.7\Omega, V_{GS} = 10V$ (see test circuit, Figure 5) | | 8 | | ns |
| t_f | Fall Time | | | 9 | | ns |
| t_c | Cross-over Time | | | 15 | | ns |

SOURCE DRAIN DIODE

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|--------------|-------------------------------|----------------------------------------------------------------------------------------------------------|------|------|------|---------|
| I_{SD} | Source-drain Current | | | | 3 | A |
| $I_{SDM(2)}$ | Source-drain Current (pulsed) | | | | 12 | A |
| $V_{SD(1)}$ | Forward On Voltage | $I_{SD} = 3A, V_{GS} = 0$ | | | 1.5 | V |
| t_{rr} | Reverse Recovery Time | $I_{SD} = 3A, di/dt = 100A/\mu s,$ $V_{DD} = 100V, T_j = 25^\circ C$ (see test circuit, Figure 5) | | 210 | | ns |
| Q_{rr} | Reverse Recovery Charge | | | 790 | | nC |
| I_{RRM} | Reverse Recovery Current | | | 7.5 | | A |
| t_{rr} | Reverse Recovery Time | $I_{SD} = 3A, di/dt = 100A/\mu s,$ $V_{DD} = 100V, T_j = 150^\circ C$ (see test circuit, Figure 5) | | 282 | | ns |
| Q_{rr} | Reverse Recovery Charge | | | 1.1 | | μC |
| I_{RRM} | Reverse Recovery Current | | | 7.7 | | A |

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
 2. Pulse width limited by safe operating area.

GATE-SOURCE ZENER DIODE

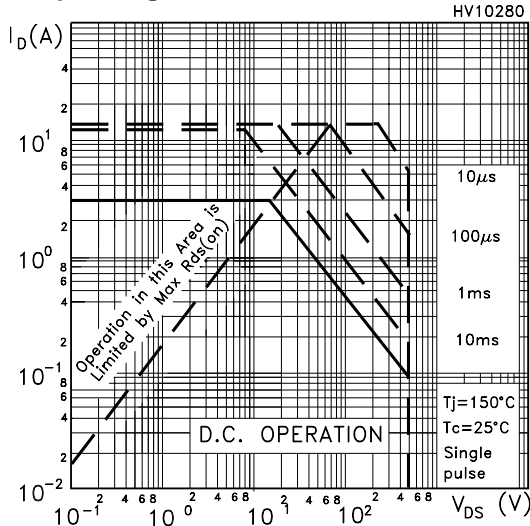
| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|------------|-------------------------------|---------------------------------|------|------|------|------|
| BV_{GSO} | Gate-Source Breakdown Voltage | $I_{GS} = \pm 1mA$ (Open Drain) | 30 | | | V |

PROTECTION FEATURES OF GATE-TO-SOURCE ZENER DIODES

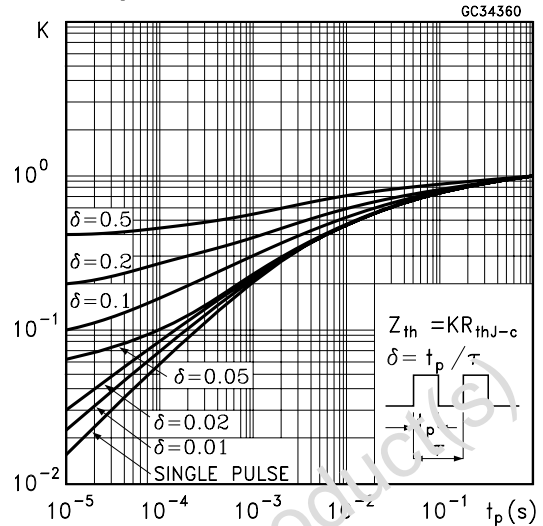
The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

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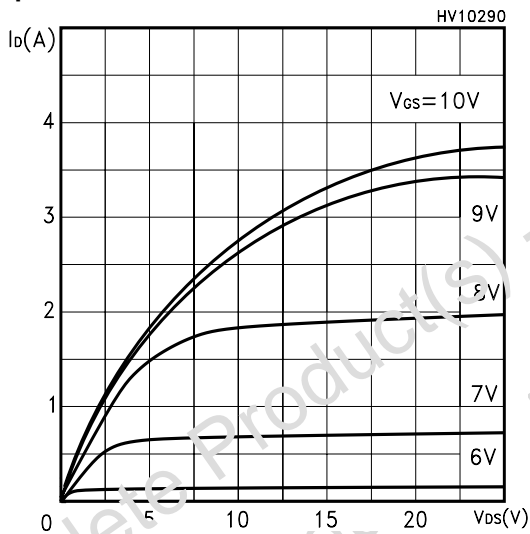
Safe Operating Area For DPAK / IPAK



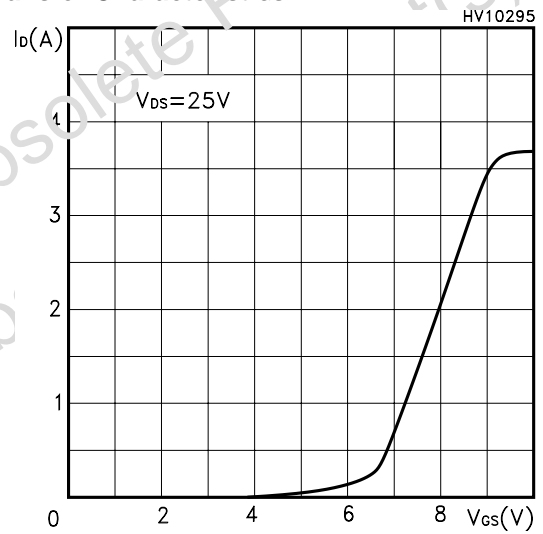
Thermal Impedance For DPAK / IPAK



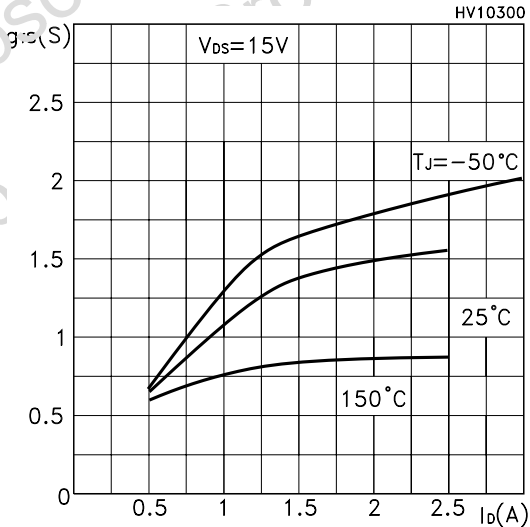
Output Characteristics



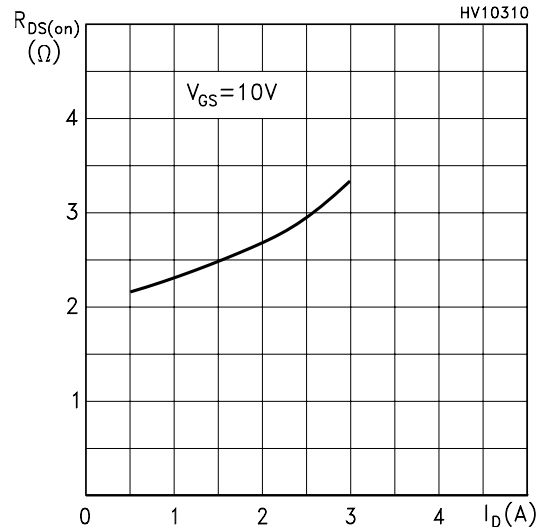
Transfer Characteristics



Transconductance

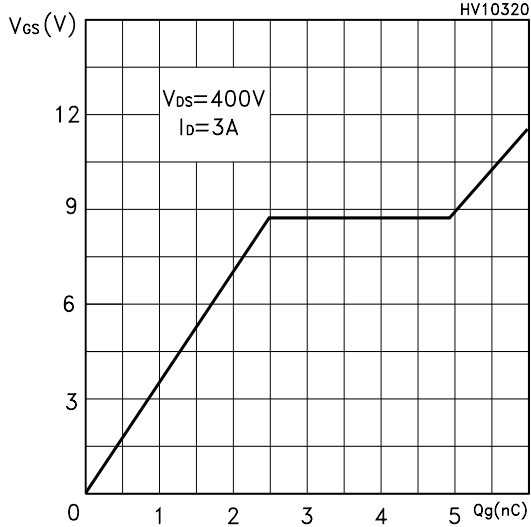


Static Drain-source On Resistance

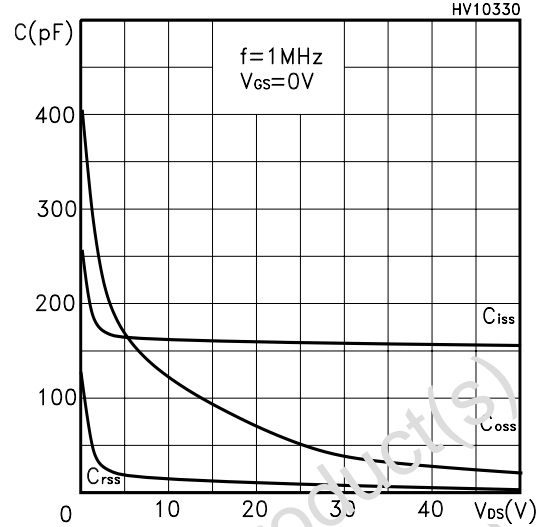


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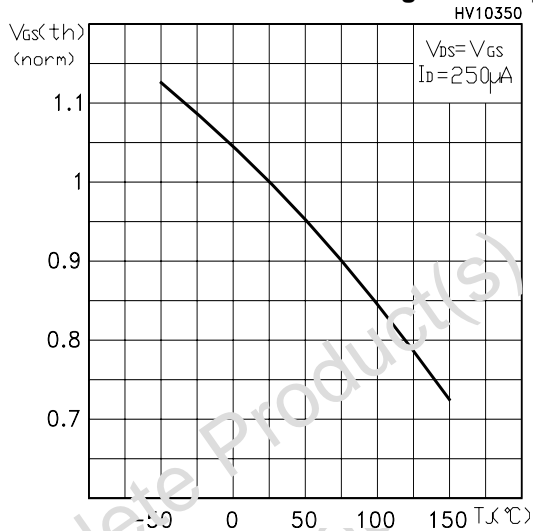
Gate Charge vs Gate-source Voltage



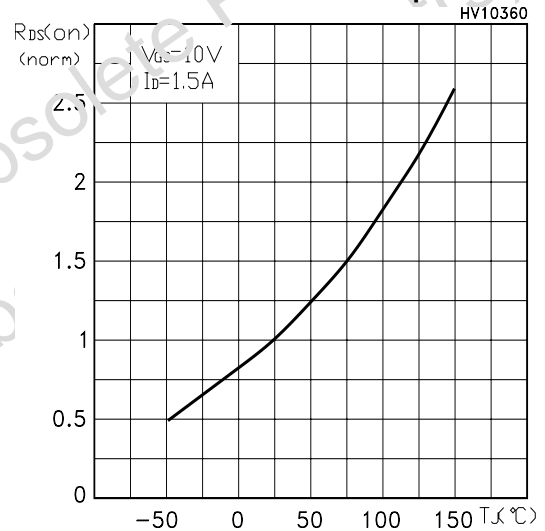
Capacitance Variations



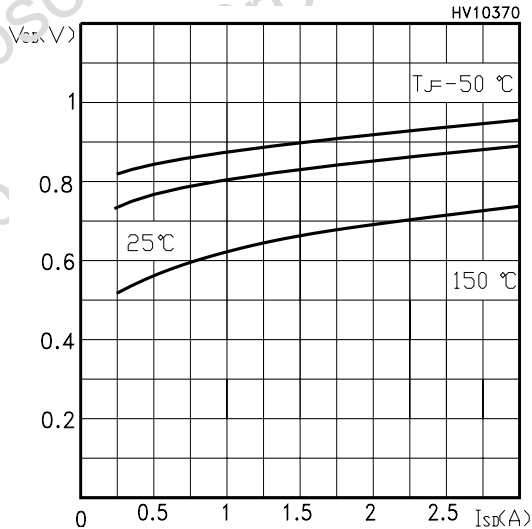
Normalized Gate Threshold Voltage vs Temp.



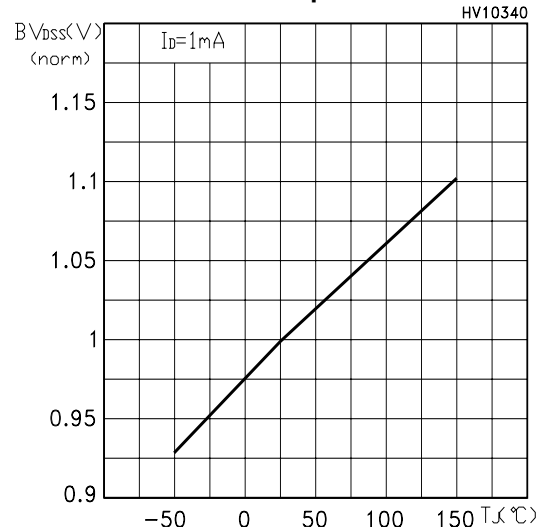
Normalized On Resistance vs Temperature



Source-Drain Diode Forward Characteristics



Normalized BVdss vs Temperature



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Fig. 1: Unclamped Inductive Load Test Circuit

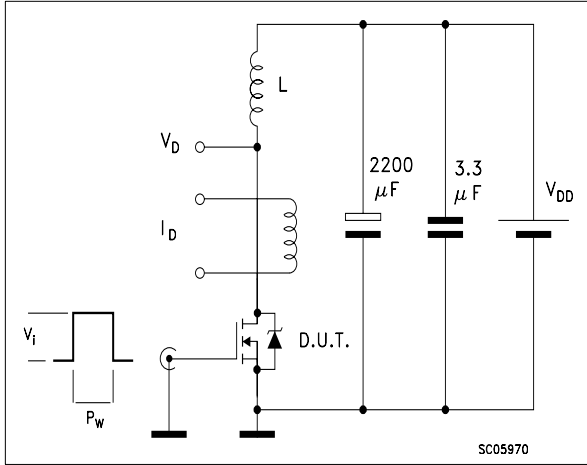


Fig. 2: Unclamped Inductive Waveform

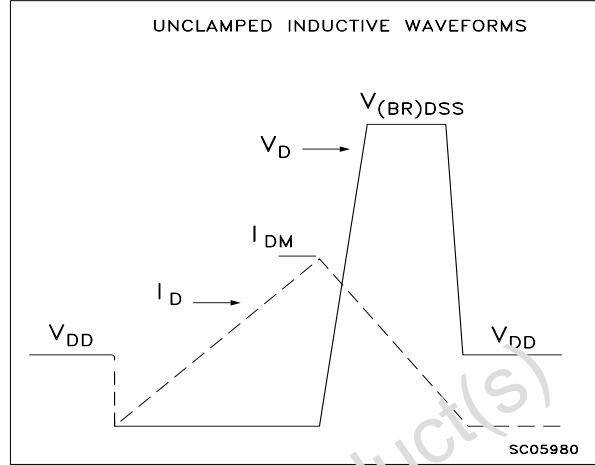


Fig. 3: Switching Times Test Circuit For Resistive Load

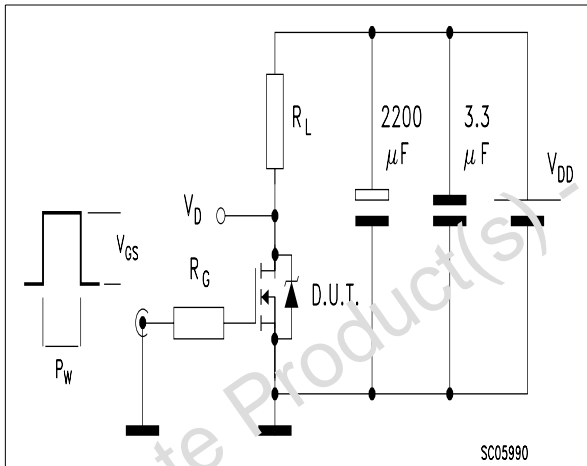


Fig. 4: Gate Charge test Circuit

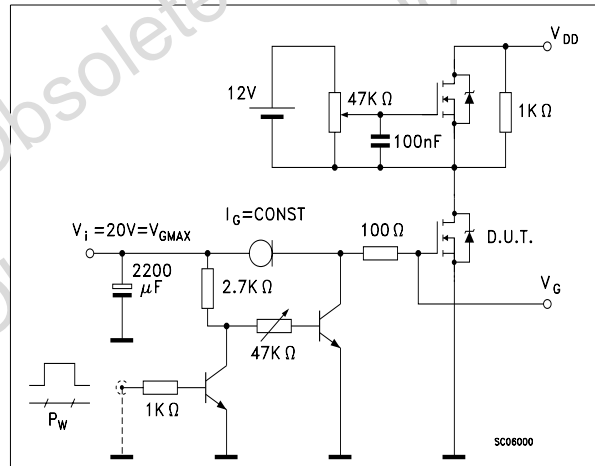
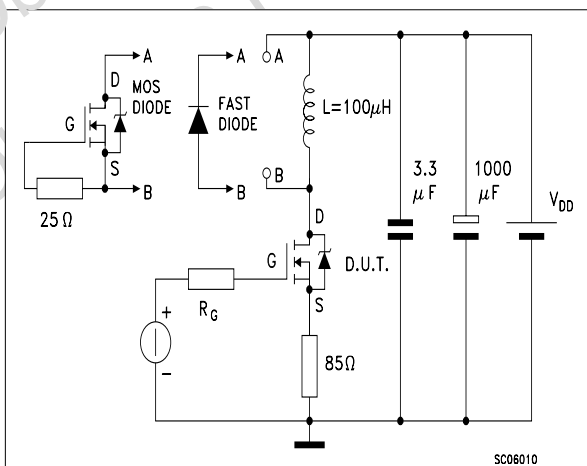


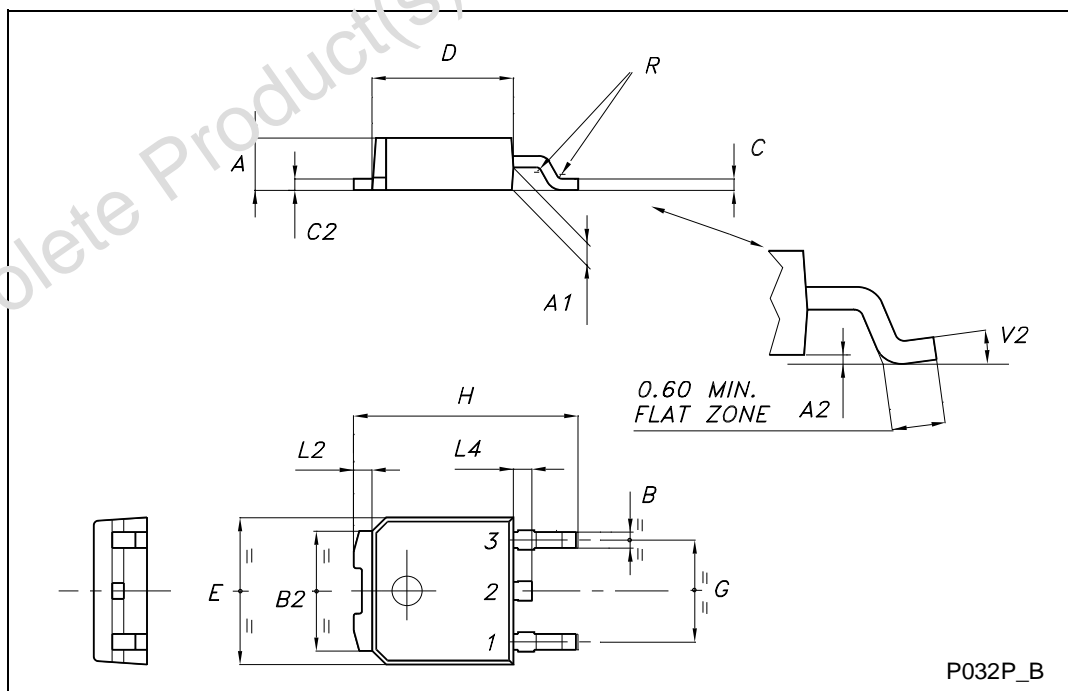
Fig. 5 Test Circuit For Inductive Load Switching And Diode Recovery Times



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TO-252 (DPAK) MECHANICAL DATA

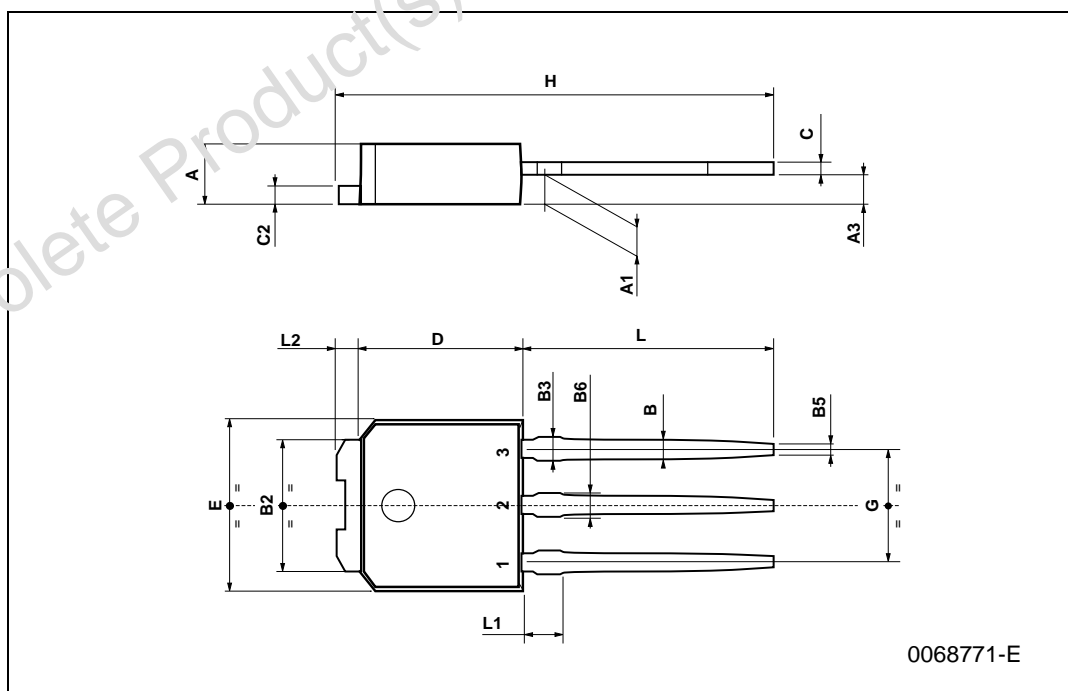
| DIM. | mm | | | inch | | |
|------|------|------|-------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 2.20 | | 2.40 | 0.087 | | 0.094 |
| A1 | 0.90 | | 1.10 | 0.035 | | 0.043 |
| A2 | 0.03 | | 0.23 | 0.001 | | 0.009 |
| B | 0.64 | | 0.90 | 0.025 | | 0.035 |
| B2 | 5.20 | | 5.40 | 0.204 | | 0.213 |
| C | 0.45 | | 0.60 | 0.018 | | 0.024 |
| C2 | 0.48 | | 0.60 | 0.019 | | 0.024 |
| D | 6.00 | | 6.20 | 0.236 | | 0.244 |
| E | 6.40 | | 6.60 | 0.252 | | 0.260 |
| G | 4.40 | | 4.60 | 0.173 | | 0.181 |
| H | 9.35 | | 10.10 | 0.368 | | 0.398 |
| L2 | | 0.8 | | | 0.031 | |
| L4 | 0.60 | | 1.00 | 0.024 | | 0.039 |
| V2 | 0° | | 8° | 0° | | 0° |



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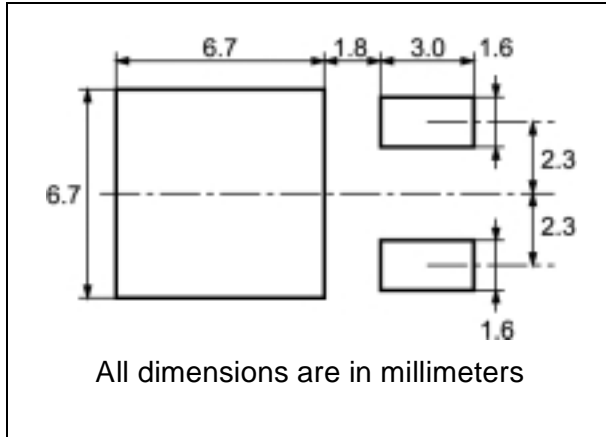
TO-251 (IPAK) MECHANICAL DATA

| DIM. | mm | | | inch | | |
|------|------|------|------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 2.2 | | 2.4 | 0.086 | | 0.094 |
| A1 | 0.9 | | 1.1 | 0.035 | | 0.043 |
| A3 | 0.7 | | 1.3 | 0.027 | | 0.051 |
| B | 0.64 | | 0.9 | 0.025 | | 0.031 |
| B2 | 5.2 | | 5.4 | 0.204 | | 0.212 |
| B3 | | | 0.85 | | | 0.033 |
| B5 | | 0.3 | | | 0.012 | |
| B6 | | | 0.95 | | | 0.037 |
| C | 0.45 | | 0.6 | 0.017 | | 0.023 |
| C2 | 0.48 | | 0.6 | 0.019 | | 0.023 |
| D | 6 | | 6.2 | 0.231 | | 0.244 |
| E | 6.4 | | 6.6 | 0.252 | | 0.260 |
| G | 4.4 | | 4.6 | 0.173 | | 0.181 |
| H | 15.9 | | 16.3 | 0.626 | | 0.641 |
| L | 9 | | 9.4 | 0.354 | | 0.370 |
| L1 | 0.8 | | 1.2 | 0.031 | | 0.047 |
| L2 | | 0.8 | 1 | | 0.031 | 0.039 |

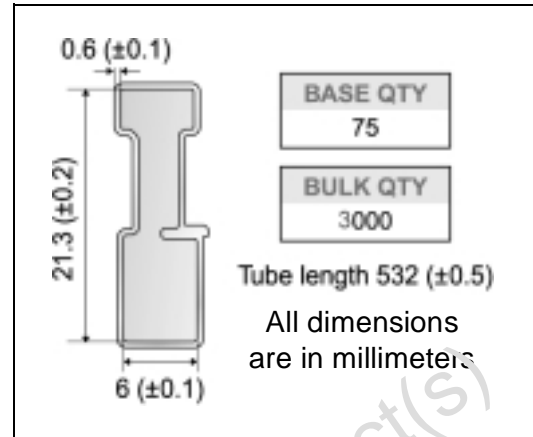


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DPAK FOOTPRINT



TUBE SHIPMENT (no suffix)*



TAPE AND REEL SHIPMENT (suffix "T4")

40 mm min. Access hole at slot location

Full radius

Tape slot in core for tape start 25mm min. width

G measured at hub

REEL MECHANICAL DATA

| DIM. | mm | | inch | |
|------|------|------|-------|--------|
| | MIN. | MAX. | MIN. | MAX. |
| A | | 330 | | 12.992 |
| B | 1.5 | | 0.059 | |
| C | 12.8 | 13.2 | 0.504 | 0.520 |
| D | 20.2 | | 0.795 | |
| G | 16.4 | 18.4 | 0.645 | 0.724 |
| N | 50 | | 1.968 | |
| T | | 22.4 | | 0.881 |

BASE QTY 2500 **BULK QTY** 2500

TAPE MECHANICAL DATA

| DIM. | mm | | inch | |
|------|------|------|-------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| A0 | 6.8 | 7 | 0.267 | 0.275 |
| B0 | 10.4 | 10.6 | 0.409 | 0.417 |
| B1 | | 12.1 | | 0.476 |
| D | 1.5 | 1.6 | 0.059 | 0.063 |
| D1 | 1.5 | | 0.059 | |
| E | 1.65 | 1.85 | 0.065 | 0.073 |
| F | 7.4 | 7.6 | 0.291 | 0.299 |
| K0 | 2.55 | 2.75 | 0.100 | 0.108 |
| P0 | 3.9 | 4.1 | 0.153 | 0.161 |
| P1 | 7.9 | 8.1 | 0.311 | 0.319 |
| P2 | 1.9 | 2.1 | 0.075 | 0.082 |
| R | 40 | | 1.574 | |
| W | 15.7 | 16.3 | 0.618 | 0.641 |

TOP COVER TAPE

Center line of cavity

User Direction of Feed

TRL

FEED DIRECTION

Bending radius R min.

* on sales type

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